

**Characterisation of 1200 V RB-IGBTs with different irradiation levels under hard and soft switching conditions**

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<https://ieeexplore.ieee.org/document/8515535>

**Comparison of the power losses in 1700V Si IGBT and SiC MOSFET modules including reverse conduction [Electronic resource]**

**Rabkowski, Jacek;** Platek, Tadeusz EPE'15 ECCE Europe : 8-10 September 2015, Geneva, Switzerland : 17th European Conference on Power Electronics and Applications 2015 / [10] p. : ill. [USB] <http://dx.doi.org/10.1109/EPE.2015.7309444>

**Operation of Single-Chip MOSFET and IGBT Devices after failure due to repetitive avalanche [Electronic resource]**

**Blinov, Andrei;** Norrga, Staffan; Tibola, Gabriel EPE'15 ECCE Europe : 8-10 September 2015, Geneva, Switzerland : 17th European Conference on Power Electronics and Applications 2015 / p. 1-9 : ill. [USB] <http://dx.doi.org/10.1109/EPE.2015.7309190>